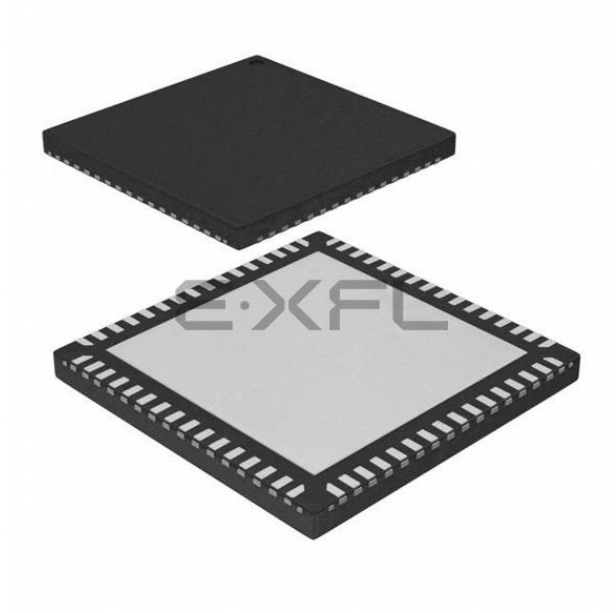
Silicon Labs - EFM32GG11B510F2048GM64-B Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	53
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 16x12b SAR; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFQFN Exposed Pad
Supplier Device Package	64-QFN (9x9)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32gg11b510f2048gm64-b

- **Timers/Counters**
  - 7× 16-bit Timer/Counter
    - 3 + 4 Compare/Capture/PWM channels (4 + 4 on one timer instance)
    - Dead-Time Insertion on several timer instances
  - 4× 32-bit Timer/Counter
  - 32-bit Real Time Counter and Calendar (RTCC)
  - 24-bit Real Time Counter (RTC)
  - 32-bit Ultra Low Energy CRYOTIMER for periodic wakeup from any Energy Mode
  - 2× 16-bit Low Energy Timer for waveform generation
  - 3× 16-bit Pulse Counter with asynchronous operation
  - 2× Watchdog Timer with dedicated RC oscillator
- **Low Energy Sensor Interface (LESENSE)**
  - Autonomous sensor monitoring in Deep Sleep Mode
  - Wide range of sensors supported, including LC sensors and capacitive buttons
  - Up to 16 inputs
- **Ultra efficient Power-on Reset and Brown-Out Detector**
- **Debug Interface**
  - 2-pin Serial Wire Debug interface
  - 1-pin Serial Wire Viewer
  - 4-pin JTAG interface
  - Embedded Trace Macrocell (ETM)
- **Pre-Programmed USB/UART Bootloader**
- **Wide Operating Range**
  - 1.8 V to 3.8 V single power supply
  - Integrated DC-DC, down to 1.8 V output with up to 200 mA load current for system
  - Standard (-40 °C to 85 °C T_{AMB}) and Extended (-40 °C to 125 °C T_J) temperature grades available
- **Packages**
  - QFN64 (9x9 mm)
  - TQFP64 (10x10 mm)
  - TQFP100 (14x14 mm)
  - BGA112 (10x10 mm)
  - BGA120 (7x7 mm)
  - BGA152 (8x8 mm)
  - BGA192 (7x7mm)

4.1.1 Absolute Maximum Ratings

Stresses above those listed below may cause permanent damage to the device. This is a stress rating only and functional operation of the devices at those or any other conditions above those indicated in the operation listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability. For more information on the available quality and reliability data, see the Quality and Reliability Monitor Report at http://www.silabs.com/support/quality/pages/default.aspx.

Table 4.1. Absolute Maximum Ratings

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Storage temperature range	T_{STG}		-50	—	150	°C
Voltage on supply pins other than VREGI and VBUS	V_{DDMAX}		-0.3	—	3.8	V
Voltage ramp rate on any supply pin	$V_{DDRAMPMAX}$		—	—	1	V / µs
DC voltage on any GPIO pin	V_{DIGPIN}	5V tolerant GPIO pins[1 2 3]	-0.3	—	Min of 5.25 and IOVDD +2	V
		LCD pins[3]	-0.3	—	Min of 3.8 and IOVDD +2	V
		Standard GPIO pins	-0.3	—	IOVDD+0.3	V
Total current into VDD power lines	I_{VDDMAX}	Source	—	—	200	mA
Total current into VSS ground lines	I_{VSSMAX}	Sink	—	—	200	mA
Current per I/O pin	I_{IOMAX}	Sink	—	—	50	mA
		Source	—	—	50	mA
Current for all I/O pins	$I_{IOALLMAX}$	Sink	—	—	200	mA
		Source	—	—	200	mA
Junction temperature	T_J	-G grade devices	-40	—	105	°C
		-I grade devices	-40	—	125	°C
Voltage on regulator supply pins VREGI and VBUS	V_{VREGI}		-0.3	—	5.5	V

Note:

1. When a GPIO pin is routed to the analog module through the APORT, the maximum voltage = IOVDD.
2. Valid for IOVDD in valid operating range or when IOVDD is undriven (high-Z). If IOVDD is connected to a low-impedance source below the valid operating range (e.g. IOVDD shorted to VSS), the pin voltage maximum is IOVDD + 0.3 V, to avoid exceeding the maximum IO current specifications.
3. To operate above the IOVDD supply rail, over-voltage tolerance must be enabled according to the GPIO_Px_OVTDIS register. Pins with over-voltage tolerance disabled have the same limits as Standard GPIO.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit

Note:

1. The minimum voltage required in bypass mode is calculated using R_{BYP} from the DCDC specification table. Requirements for other loads can be calculated as $V_{DVDD\_min}+I_{LOAD} * R_{BYP\_max}$.
2. VREGVDD must be tied to AVDD. Both VREGVDD and AVDD minimum voltages must be satisfied for the part to operate.
3. The system designer should consult the characteristic specs of the capacitor used on DECOUPLE to ensure its capacitance value stays within the specified bounds across temperature and DC bias.
4. VSCALE0 to VSCALE2 voltage change transitions occur at a rate of 10 mV / usec for approximately 20 usec. During this transition, peak currents will be dependent on the value of the DECOUPLE output capacitor, from 35 mA (with a 1 µF capacitor) to 70 mA (with a 2.7 µF capacitor).
5. When the CSEN peripheral is used with chopping enabled (CSEN_CTRL_CHOPEN = ENABLE), IOVDD must be equal to AVDD.
6. The maximum limit on T_A may be lower due to device self-heating, which depends on the power dissipation of the specific application. T_A (max) = T_J (max) - ($THETA_{JA}$ x PowerDissipation). Refer to the Absolute Maximum Ratings table and the Thermal Characteristics table for T_J and $THETA_{JA}$.

4.1.3 Thermal Characteristics

Table 4.3. Thermal Characteristics

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Thermal resistance, QFN64 Package	$THETA_{JA\_QFN64}$	4-Layer PCB, Air velocity = 0 m/s	—	17.8	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	15.4	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	13.8	—	°C/W
Thermal resistance, TQFP64 Package	$THETA_{JA\_TQFP64}$	4-Layer PCB, Air velocity = 0 m/s	—	33.9	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	32.1	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	30.1	—	°C/W
Thermal resistance, TQFP100 Package	$THETA_{JA\_TQFP100}$	4-Layer PCB, Air velocity = 0 m/s	—	44.1	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	37.7	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	35.5	—	°C/W
Thermal resistance, BGA112 Package	$THETA_{JA\_BGA112}$	4-Layer PCB, Air velocity = 0 m/s	—	42.0	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	37.0	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	35.3	—	°C/W
Thermal resistance, BGA120 Package	$THETA_{JA\_BGA120}$	4-Layer PCB, Air velocity = 0 m/s	—	47.9	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	41.8	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	39.6	—	°C/W
Thermal resistance, BGA152 Package	$THETA_{JA\_BGA152}$	4-Layer PCB, Air velocity = 0 m/s	—	35.7	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	31.0	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	29.5	—	°C/W
Thermal resistance, BGA192 Package	$THETA_{JA\_BGA192}$	4-Layer PCB, Air velocity = 0 m/s	—	47.9	—	°C/W
		4-Layer PCB, Air velocity = 1 m/s	—	41.8	—	°C/W
		4-Layer PCB, Air velocity = 2 m/s	—	39.6	—	°C/W

4.1.4 DC-DC Converter

Test conditions: L_DCDC=4.7 µH (Murata LQH3NPN4R7MM0L), C_DCDC=4.7 µF (Samsung CL10B475KQ8NQNC), V_DCDC_I=3.3 V, V_DCDC_O=1.8 V, I_DCDC_LOAD=50 mA, Heavy Drive configuration, F_DCDC_LN=7 MHz, unless otherwise indicated.

Table 4.4. DC-DC Converter

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Input voltage range	V_{DCDC_I}	Bypass mode, I_{DCDC_LOAD} = 50 mA	1.8	—	$V_{VREGVDD\_MAX}$	V
		Low noise (LN) mode, 1.8 V output, I_{DCDC_LOAD} = 100 mA, or Low power (LP) mode, 1.8 V output, I_{DCDC_LOAD} = 10 mA	2.4	—	$V_{VREGVDD\_MAX}$	V
		Low noise (LN) mode, 1.8 V output, I_{DCDC_LOAD} = 200 mA	2.6	—	$V_{VREGVDD\_MAX}$	V
Output voltage programmable range[1]	V_{DCDC_O}		1.8	—	$V_{VREGVDD}$	V
Regulation DC accuracy	ACC_{DC}	Low Noise (LN) mode, 1.8 V target output	TBD	—	TBD	V
Regulation window[4]	WIN_{REG}	Low Power (LP) mode, LPCMPBIASEMxx[3] = 0, 1.8 V target output, I_{DCDC_LOAD} ≤ 75 µA	TBD	—	TBD	V
		Low Power (LP) mode, LPCMPBIASEMxx[3] = 3, 1.8 V target output, I_{DCDC_LOAD} ≤ 10 mA	TBD	—	TBD	V
Steady-state output ripple	V_R		—	3	—	mVpp
Output voltage under/overshoot	V_{OV}	CCM Mode (LNFORCECCM[3] = 1), Load changes between 0 mA and 100 mA	—	25	TBD	mV
		DCM Mode (LNFORCECCM[3] = 0), Load changes between 0 mA and 10 mA	—	45	TBD	mV
		Overshoot during LP to LN CCM/DCM mode transitions compared to DC level in LN mode	—	200	—	mV
		Undershoot during BYP/LP to LN CCM (LNFORCECCM[3] = 1) mode transitions compared to DC level in LN mode	—	40	—	mV
		Undershoot during BYP/LP to LN DCM (LNFORCECCM[3] = 0) mode transitions compared to DC level in LN mode	—	100	—	mV
DC line regulation	V_{REG}	Input changes between $V_{VREGVDD\_MAX}$ and 2.4 V	—	0.1	—	%
DC load regulation	I_{REG}	Load changes between 0 mA and 100 mA in CCM mode	—	0.1	—	%

4.1.5 5V Regulator

V_{VREGI} = 5 V, V_{VREGO} = 3.3 V, C_{VREGI} = 10 µF, C_{VREGO} = 4.7 µF, unless otherwise specified.

Table 4.5. 5V Regulator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
VREGI or VBUS input voltage range	V_{VREGI}	Regulating output	2.7	—	5.5	V
		Bypass mode enabled	2.7	—	3.8	V
VREGO output voltage	V_{VREGO}	Regulating output, 3.3 V setting	3.1	3.3	3.5	V
		EM4S open-loop output, I_{OUT} < 100 µA	1.8	—	3.8	V
Voltage output step size	V_{VREGO_SS}		—	0.1	—	V
Resistance in Bypass Mode	R_{BYP}	Bypass mode enabled	—	1.2	TBD	Ω
Output current	I_{OUT}	EM0 or EM1, V_{VREGI} > V_{VREGO} + 0.6 V	—	—	200	mA
		EM0 or EM1, V_{VREGI} > V_{VREGO} + 0.3 V	—	—	100	mA
		EM2, EM3, or EM4H, V_{VREGI} > V_{VREGO} + 0.6 V	—	—	2	mA
		EM2, EM3, or EM4H, V_{VREGI} > V_{VREGO} + 0.3 V	—	—	0.5	mA
		EM4S	—	—	20	µA
Load regulation	LR_{VREGO}	EM0 or EM1	—	0.10	—	mV/mA
		EM2, EM3, or EM4H	—	2.5	—	mV/mA
DC power supply rejection	PSR_{DC}		—	40	—	dB
VREGI or VBUS bypass capacitance	C_{VREGI}		—	10	—	µF
VREGO bypass capacitance	C_{VREGO}		1	4.7	10	µF
Supply current consumption	I_{VREGI}	EM0 or EM1, No load	—	29	—	µA
		EM2, EM3, or EM4H, No load	—	270	—	nA
		EM4S, No load	—	70	—	nA
VREGI and VBUS detection high threshold	V_{DET_H}		TBD	1.18	—	V
VREGI and VBUS detection low threshold	V_{DET_L}		—	1.12	TBD	V
Current monitor transfer ratio	$IMON_{XF}$	Translation of current through VREGO path to voltage at ADC input	—	0.35	—	mA/mV

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM2 mode, with voltage scaling enabled	I_{EM2_VS}	Full 512 kB RAM retention and RTCC running from LFXO	—	3.9	—	µA
		Full 512 kB RAM retention and RTCC running from LFRCO	—	4.3	—	µA
		16 kB (1 bank) RAM retention and RTCC running from LFRCO[2]	—	2.8	TBD	µA
Current consumption in EM3 mode, with voltage scaling enabled	I_{EM3_VS}	Full 512 kB RAM retention and CRYOTIMER running from ULFRCO	—	3.6	TBD	µA
Current consumption in EM4H mode, with voltage scaling enabled	I_{EM4H_VS}	128 byte RAM retention, RTCC running from LFXO	—	1.08	—	µA
		128 byte RAM retention, CRYOTIMER running from ULFRCO	—	0.69	—	µA
		128 byte RAM retention, no RTCC	—	0.69	TBD	µA
Current consumption in EM4S mode	I_{EM4S}	No RAM retention, no RTCC	—	0.16	TBD	µA
Current consumption of peripheral power domain 1, with voltage scaling enabled	I_{PD1_VS}	Additional current consumption in EM2/3 when any peripherals on power domain 1 are enabled[1]	—	0.68	—	µA
Current consumption of peripheral power domain 2, with voltage scaling enabled	I_{PD2_VS}	Additional current consumption in EM2/3 when any peripherals on power domain 2 are enabled[1]	—	0.28	—	µA

Note:

1. Extra current consumed by power domain. Does not include current associated with the enabled peripherals. See 3.2.4 EM2 and EM3 Power Domains for a list of the peripherals in each power domain.
2. CMU_LFRCOCTRL_ENVREF = 1, CMU_LFRCOCTRL_VREFUPDATE = 1

4.1.11 Flash Memory Characteristics[5]

Table 4.19. Flash Memory Characteristics[5]

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Flash erase cycles before failure	EC_{FLASH}		10000	—	—	cycles
Flash data retention	RET_{FLASH}	T ≤ 85 °C	10	—	—	years
		T ≤ 125 °C	10	—	—	years
Word (32-bit) programming time	t_{W_PROG}	Burst write, 128 words, average time per word	20	26.2	32	µs
		Single word	59	68.7	83	µs
Page erase time[4]	t_{PERASE}		20	26.8	35	ms
Mass erase time[1]	t_{MERASE}		20	26.9	35	ms
Device erase time[2 3]	t_{DERASE}	T ≤ 85 °C	—	80.7	95	ms
		T ≤ 125 °C	—	80.7	100	ms
Erase current[6]	I_{ERASE}	Page Erase	—	—	1.7	mA
		Mass or Device Erase	—	—	2.1	mA
Write current[6]	I_{WRITE}		—	—	3.9	mA
Supply voltage during flash erase and write	V_{FLASH}		1.62	—	3.6	V

Note:

1. Mass erase is issued by the CPU and erases all flash.
2. Device erase is issued over the AAP interface and erases all flash, SRAM, the Lock Bit (LB) page, and the User data page Lock Word (ULW).
3. From setting the DEVICEERASE bit in AAP_CMD to 1 until the ERASEBUSY bit in AAP_STATUS is cleared to 0. Internal setup and hold times for flash control signals are included.
4. From setting the ERASEPAGE bit in MSC_WRITECMD to 1 until the BUSY bit in MSC_STATUS is cleared to 0. Internal setup and hold times for flash control signals are included.
5. Flash data retention information is published in the Quarterly Quality and Reliability Report.
6. Measured at 25 °C.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
MISO hold time [1] [3]	t_{H_MI}	USART2, location 4, IOVDD = 1.8 V	-11.6	—	—	ns
		USART2, location 4, IOVDD = 3.0 V	-11.6	—	—	ns
		USART2, location 5, IOVDD = 1.8 V	-9.1	—	—	ns
		USART2, location 5, IOVDD = 3.0 V	-9.1	—	—	ns
		All other USARTs and locations, IOVDD = 1.8 V	-8	—	—	ns
		All other USARTs and locations, IOVDD = 3.0 V	-8	—	—	ns

Note:

1. Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0).
2. $t_{HFPERCLK}$ is one period of the selected HFPERCLK.
3. Measurement done with 8 pF output loading at 10% and 90% of V_{DD} (figure shows 50% of V_{DD}).

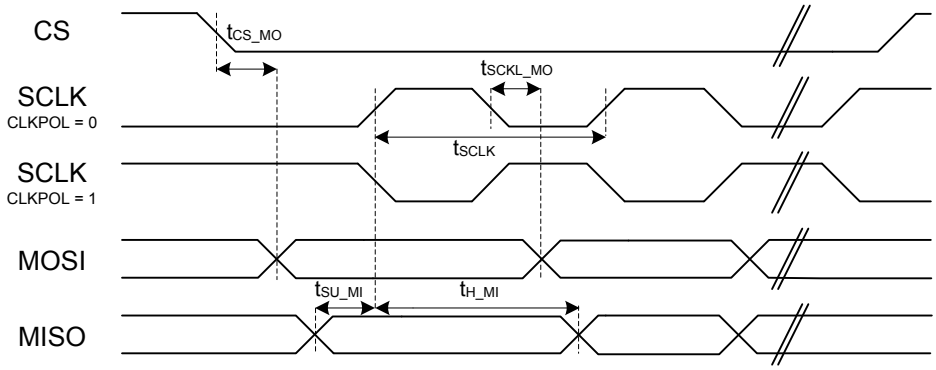

Figure 4.1. SPI Master Timing Diagram

EBI Read Enable Output Timing

Timing applies to both EBI_REn and EBI_NANDREn for all addressing modes and both polarities. Output timing for EBI_AD applies only to multiplexed addressing modes D8A24ALE and D16A16ALE. All numbers are based on route locations 0,1,2 only (with all EBI alternate functions using the same location at the same time). Timing is specified at 10% and 90% of IOVDD, 25 pF external loading, and slew rate for all GPIO set to 6.

Table 4.38. EBI Read Enable Output Timing

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Output hold time, from trailing EBI_REn / EBI_NANDREn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	t_{OH_REn}	IOVDD ≥ 1.62 V	-23 + (RDHOLD * $t_{HFCORECLK}$)	—	—	ns
		IOVDD ≥ 3.0 V	-13 + (RDHOLD * $t_{HFCORECLK}$)	—	—	ns
Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_REn / EBI_NANDREn edge [1]	t_{OSU_REn}	IOVDD ≥ 1.62 V	-12 + (RDSETUP * $t_{HFCORECLK}$)	—	—	ns
		IOVDD ≥ 3.0 V	-11 + (RDSETUP * $t_{HFCORECLK}$)	—	—	ns
EBI_REn pulse width[1] [2]	t_{WIDTH_REn}	IOVDD ≥ 1.62 V	-6 + (MAX(1, RDSTRB) * $t_{HFCORECLK}$)	—	—	ns
		IOVDD ≥ 3.0 V	-4 + (MAX(1, RDSTRB) * $t_{HFCORECLK}$)	—	—	ns

Note:

1. The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFRE=0. The leading edge of EBI_REn can be moved to the right by setting HALFRE=1. This decreases the length of t_{WIDTH_REn} and increases the length of t_{OSU_REn} by 1/2 * $t_{HFCLKNODIV}$.
2. When page mode is used, RDSTRB is replaced by RDPA for page hits.

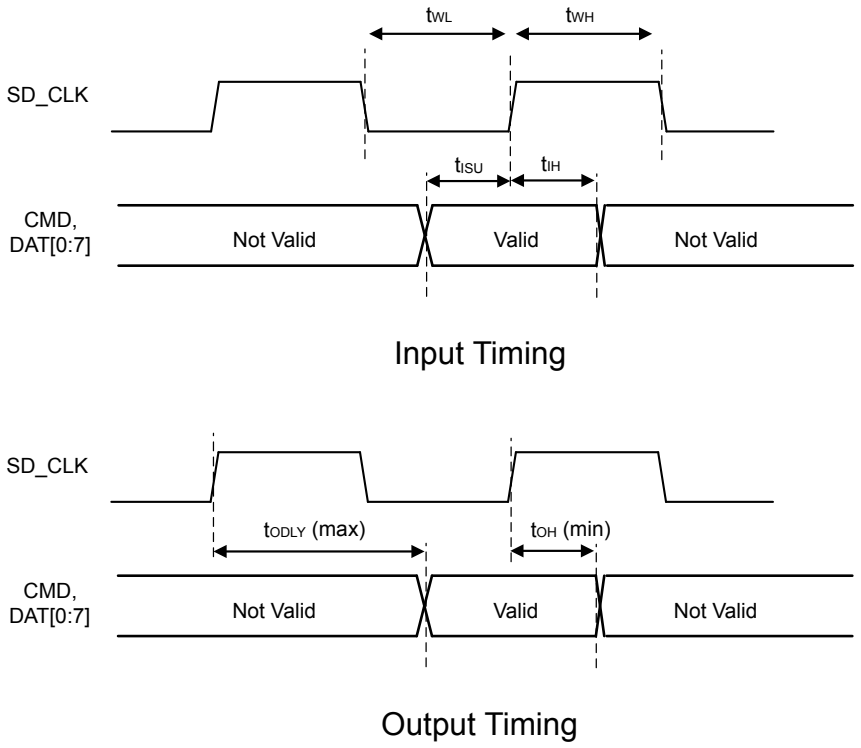

Figure 4.17. SDIO MMC SDR Mode Timing

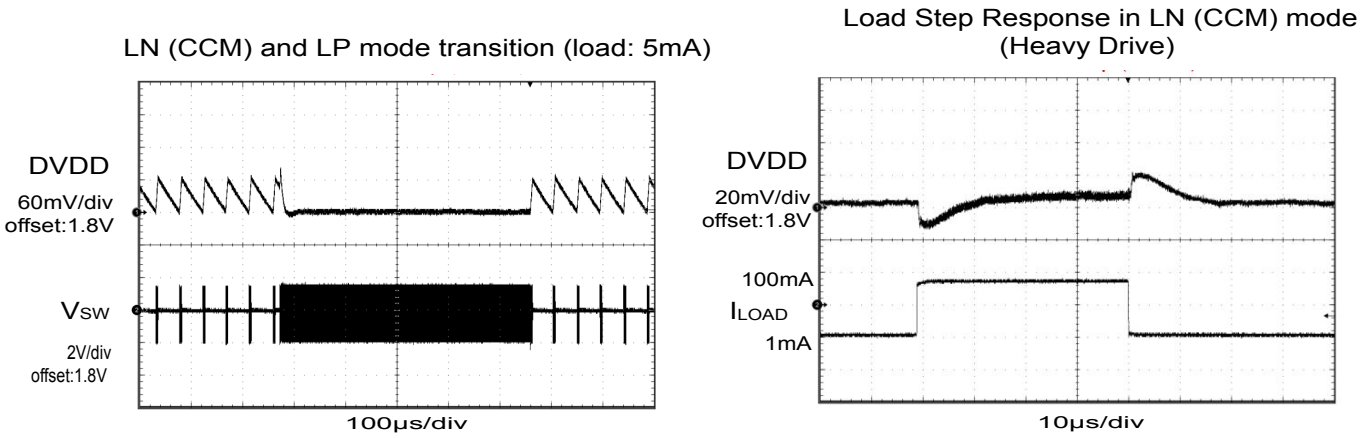

Figure 4.30. DC-DC Converter Transition Waveforms

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PF11	A13	GPIO (5V)	PA15	B1	GPIO
PE13	B2	GPIO	PE11	B3	GPIO
PE8	B4	GPIO	PD12	B5	GPIO
PD10	B6	GPIO	PF8	B7	GPIO
PF6	B8	GPIO	PF13	B9	GPIO (5V)
PF4	B10	GPIO	PF3	B11	GPIO
VBUS	B12	USB VBUS signal and auxiliary input to 5 V regulator.	PF10	B13	GPIO (5V)
PA1	C1	GPIO	PA0	C2	GPIO
PE10	C3	GPIO	PD13	C4	GPIO (5V)
VSS	C5 C8 H3 J3 K11 L12 L15	Ground	IOVDD1	C6	Digital IO power supply 1.
PF9	C7	GPIO	IOVDD0	C9 J11 K3 L11 L16	Digital IO power supply 0.
PF2	C10	GPIO	PF1	C11	GPIO (5V)
PC14	C12	GPIO (5V)	PC15	C13	GPIO (5V)
PA3	D1	GPIO	PA2	D2	GPIO
PB15	D3	GPIO (5V)	PF0	D11	GPIO (5V)
PC12	D12	GPIO (5V)	PC13	D13	GPIO (5V)
PA6	E1	GPIO	PA5	E2	GPIO
PA4	E3	GPIO	PC9	E11	GPIO (5V)
PC10	E12	GPIO (5V)	PC11	E13	GPIO (5V)
PB0	F1	GPIO	PB1	F2	GPIO
PB2	F3	GPIO	PE6	F11	GPIO
PE7	F12	GPIO	PC8	F13	GPIO (5V)
PB3	G1	GPIO	PB4	G2	GPIO
IOVDD2	G3	Digital IO power supply 2.	PE3	G11	GPIO
PE4	G12	GPIO	PE5	G13	GPIO
PB5	H1	GPIO	PB6	H2	GPIO
DVDD	H11	Digital power supply.	PE2	H12	GPIO
DECOUPLE	H13	Decouple output for on-chip voltage regulator. An external decoupling capacitor is required at this pin.	PD14	J1	GPIO (5V)
PD15	J2	GPIO (5V)	PE1	J12	GPIO (5V)

5.4 EFM32GG11B5xx in BGA120 Device Pinout

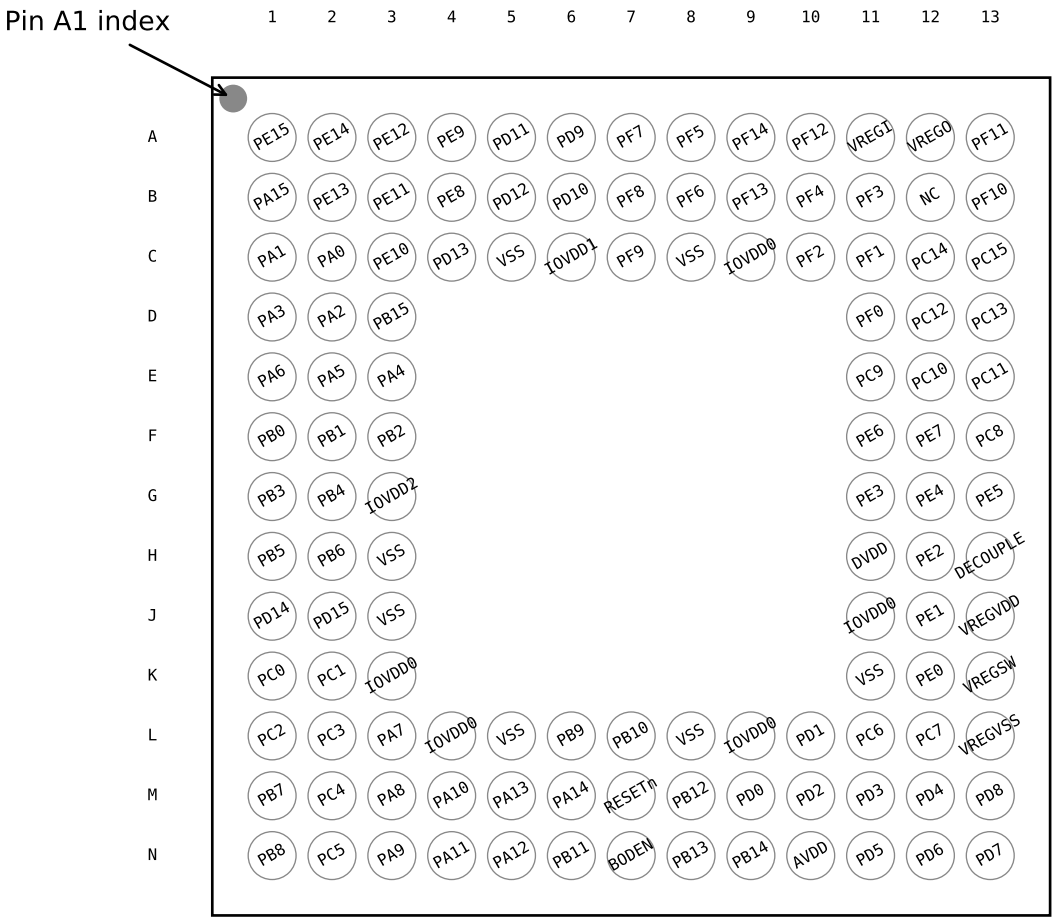

Figure 5.4. EFM32GG11B5xx in BGA120 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.20 GPIO Functionality Table or 5.21 Alternate Functionality Overview.

Table 5.4. EFM32GG11B5xx in BGA120 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE15	A1	GPIO	PE14	A2	GPIO
PE12	A3	GPIO	PE9	A4	GPIO
PD11	A5	GPIO	PD9	A6	GPIO
PF7	A7	GPIO	PF5	A8	GPIO
PF14	A9	GPIO (5V)	PF12	A10	GPIO
VREGI	A11	Input to 5 V regulator.	VREGO	A12	Decoupling for 5 V regulator and regulator output. Power for USB PHY in USB-enabled OPNs

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PC1	K2	GPIO (5V)	PE0	K12	GPIO (5V)
VREGSW	K13	DCDC regulator switching node	PC2	L1	GPIO (5V)
PC3	L2	GPIO (5V)	PA7	L3	GPIO
PB9	L13	GPIO (5V)	PB10	L14	GPIO (5V)
PD1	L17	GPIO	PC6	L18	GPIO
PC7	L19	GPIO	VREGVSS	L20	Voltage regulator VSS
PB7	M1	GPIO	PC4	M2	GPIO
PA8	M3	GPIO	PA10	M4	GPIO
PA13	M5	GPIO (5V)	PA14	M6	GPIO
RESETn	M7	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.	PB12	M8	GPIO
PD0	M9	GPIO (5V)	PD2	M10	GPIO (5V)
PD3	M11	GPIO	PD4	M12	GPIO
PD8	M13	GPIO	PB8	N1	GPIO
PC5	N2	GPIO	PA9	N3	GPIO
PA11	N4	GPIO	PA12	N5	GPIO (5V)
PB11	N6	GPIO	BODEN	N7	Brown-Out Detector Enable. This pin may be left disconnected or tied to AVDD.
PB13	N8	GPIO	PB14	N9	GPIO
AVDD	N10	Analog power supply.	PD5	N11	GPIO
PD6	N12	GPIO	PD7	N13	GPIO

Note:

1. GPIO with 5V tolerance are indicated by (5V).
2. The pins PD13, PD14, and PD15 will not be 5V tolerant on all future devices. In order to preserve upgrade options with full hardware compatibility, do not use these pins with 5V domains.

5.5 EFM32GG11B4xx in BGA120 Device Pinout

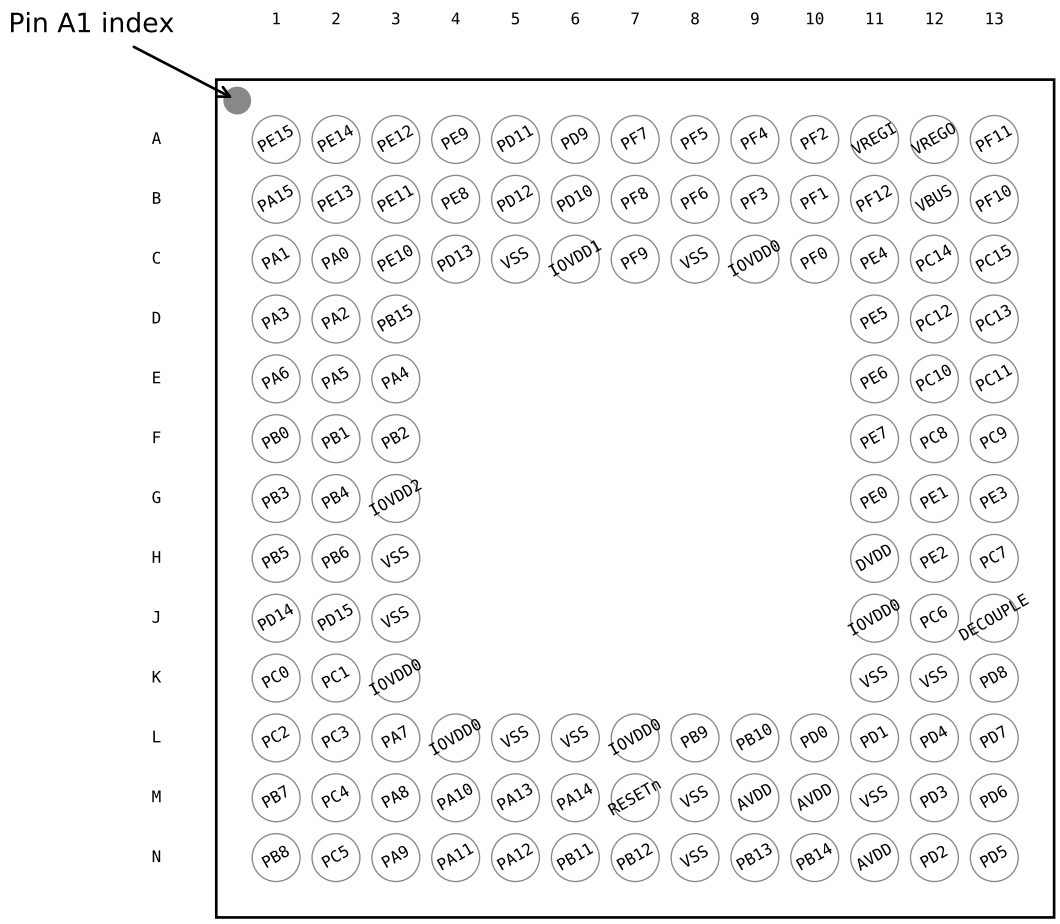

Figure 5.5. EFM32GG11B4xx in BGA120 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.20 GPIO Functionality Table or 5.21 Alternate Functionality Overview.

Table 5.5. EFM32GG11B4xx in BGA120 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE15	A1	GPIO	PE14	A2	GPIO
PE12	A3	GPIO	PE9	A4	GPIO
PD11	A5	GPIO	PD9	A6	GPIO
PF7	A7	GPIO	PF5	A8	GPIO
PF4	A9	GPIO	PF2	A10	GPIO
VREGI	A11	Input to 5 V regulator.	VREGO	A12	Decoupling for 5 V regulator and regulator output. Power for USB PHY in USB-enabled OPNs

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PE8	B4	GPIO	PD11	B5	GPIO
PF8	B6	GPIO	PF6	B7	GPIO
VBUS	B8	USB VBUS signal and auxiliary input to 5 V regulator.	PE5	B9	GPIO
VREGI	B10	Input to 5 V regulator.	VREGO	B11	Decoupling for 5 V regulator and regulator output. Power for USB PHY in USB-enabled OPNs
PA1	C1	GPIO	PA0	C2	GPIO
PE10	C3	GPIO	PD13	C4	GPIO (5V)
PD12	C5	GPIO	PF9	C6	GPIO
VSS	C7 D4 F9 G3 G9 H6 K4 K7 K10 L7	Ground	PF2	C8	GPIO
PE6	C9	GPIO	PC10	C10	GPIO (5V)
PC11	C11	GPIO (5V)	PA3	D1	GPIO
PA2	D2	GPIO	PB15	D3	GPIO (5V)
IOVDD1	D5	Digital IO power supply 1.	PD9	D6	GPIO
IOVDD0	D7 G8 H7 L4	Digital IO power supply 0.	PF1	D8	GPIO (5V)
PE7	D9	GPIO	PC8	D10	GPIO (5V)
PC9	D11	GPIO (5V)	PA6	E1	GPIO
PA5	E2	GPIO	PA4	E3	GPIO
PB0	E4	GPIO	PF0	E8	GPIO (5V)
PE0	E9	GPIO (5V)	PE1	E10	GPIO (5V)
PE3	E11	GPIO	PB1	F1	GPIO
PB2	F2	GPIO	PB3	F3	GPIO
PB4	F4	GPIO	DVDD	F8	Digital power supply.
PE2	F10	GPIO	DECOUPLE	F11	Decouple output for on-chip voltage regulator. An external decoupling capacitor is required at this pin.
PB5	G1	GPIO	PB6	G2	GPIO
IOVDD2	G4	Digital IO power supply 2.	PC6	G10	GPIO
PC7	G11	GPIO	PC0	H1	GPIO (5V)
PC2	H2	GPIO (5V)	PD14	H3	GPIO (5V)
PA7	H4	GPIO	PA8	H5	GPIO

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PC4	13	GPIO	PC5	14	GPIO
PB7	15	GPIO	PB8	16	GPIO
PA8	17	GPIO	PA12	18	GPIO (5V)
PA14	19	GPIO	RESETn	20	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.
PB11	21	GPIO	PB12	22	GPIO
AVDD	24	Analog power supply.	PB13	25	GPIO
PB14	26	GPIO	PD0	28	GPIO (5V)
PD1	29	GPIO	PD2	30	GPIO (5V)
PD3	31	GPIO	PD4	32	GPIO
PD5	33	GPIO	PD6	34	GPIO
PD8	35	GPIO	VREGVSS	36	Voltage regulator VSS
VREGSW	37	DCDC regulator switching node	VREGVDD	38	Voltage regulator VDD input
DVDD	39	Digital power supply.	DECOUPLE	40	Decouple output for on-chip voltage regulator. An external decoupling capacitor is required at this pin.
PE4	41	GPIO	PE5	42	GPIO
PE6	43	GPIO	PE7	44	GPIO
VREGI	45	Input to 5 V regulator.	VREGO	46	Decoupling for 5 V regulator and regulator output. Power for USB PHY in USB-enabled OPNs
PF10	47	GPIO (5V)	PF11	48	GPIO (5V)
PF0	49	GPIO (5V)	PF1	50	GPIO (5V)
PF2	51	GPIO	VBUS	52	USB VBUS signal and auxiliary input to 5 V regulator.
PF12	53	GPIO	PF5	54	GPIO
PE8	57	GPIO	PE9	58	GPIO
PE10	59	GPIO	PE11	60	GPIO
PE12	61	GPIO	PE13	62	GPIO
PE14	63	GPIO	PE15	64	GPIO

Note:

1. GPIO with 5V tolerance are indicated by (5V).

5.15 EFM32GG11B1xx in QFP64 Device Pinout

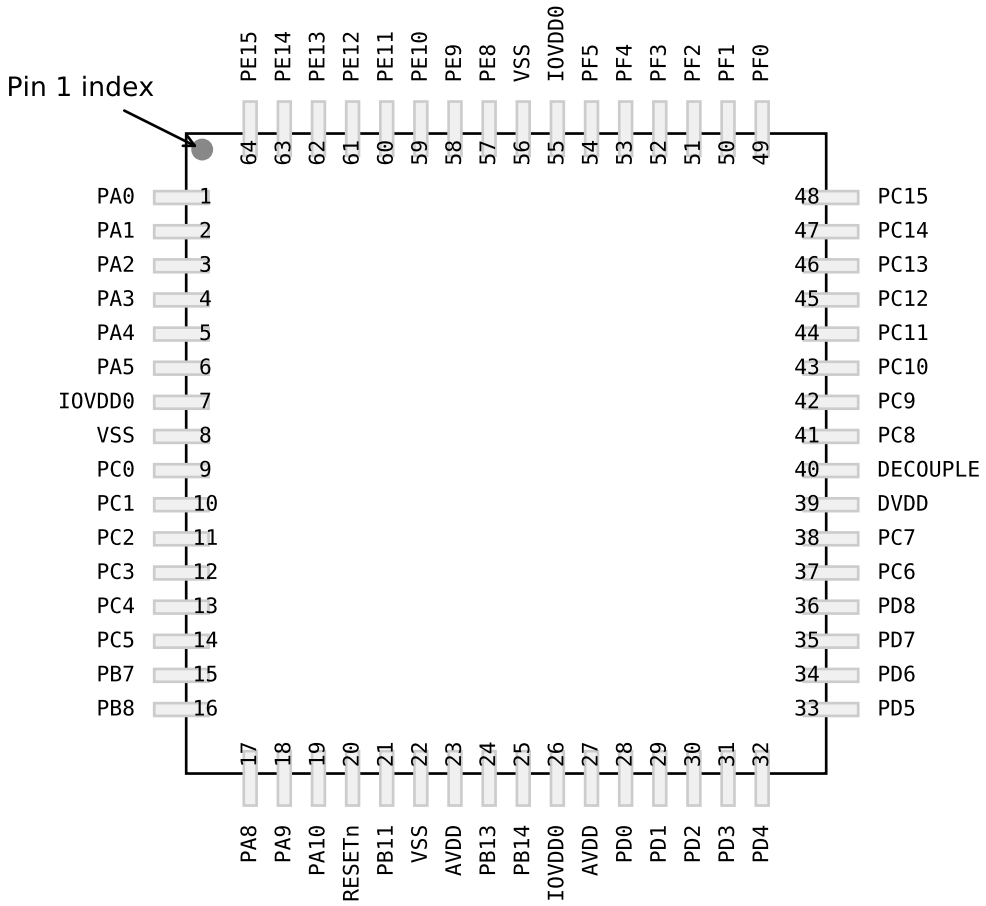

Figure 5.15. EFM32GG11B1xx in QFP64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.20 GPIO Functionality Table or 5.21 Alternate Functionality Overview.

Table 5.15. EFM32GG11B1xx in QFP64 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	PA3	4	GPIO
PA4	5	GPIO	PA5	6	GPIO
IOVDD0	7 26 55	Digital IO power supply 0.	VSS	8 22 56	Ground
PC0	9	GPIO (5V)	PC1	10	GPIO (5V)
PC2	11	GPIO (5V)	PC3	12	GPIO (5V)

Table 9.1. BGA112 Package Dimensions

Dimension	Min	Typ	Max
A	-	-	1.30
A1	0.55	0.60	0.65
A2		0.21 BSC	
A3	0.30	0.35	0.40
d	0.43	0.48	0.53
D		10.00 BSC	
D1		8.00 BSC	
E		10.00 BSC	
E1		8.00 BSC	
e1		0.80 BSC	
e2		0.80 BSC	
L1		1.00 REF	
L2		1.00 REF	

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

Table 12.1. QFN64 Package Dimensions

Dimension	Min	Typ	Max
A	0.70	0.75	0.80
A1	0.00	—	0.05
b	0.20	0.25	0.30
A3	0.203 REF		
D	9.00 BSC		
e	0.50 BSC		
E	9.00 BSC		
D2	7.10	7.20	7.30
E2	7.10	7.20	7.30
L	0.40	0.45	0.50
L1	0.00	—	0.10
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		

Note:
1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.